



TITLE: FLASH MEMORY CELL HAVING REDUCED LEAKAGE CURRENT
INVENTOR(S): Sheung Hee Park, Richard M. Fastow, and Dong-Hyuk Ju
USSN: 10/618,191 Attorney Docket #: AMD-H0534

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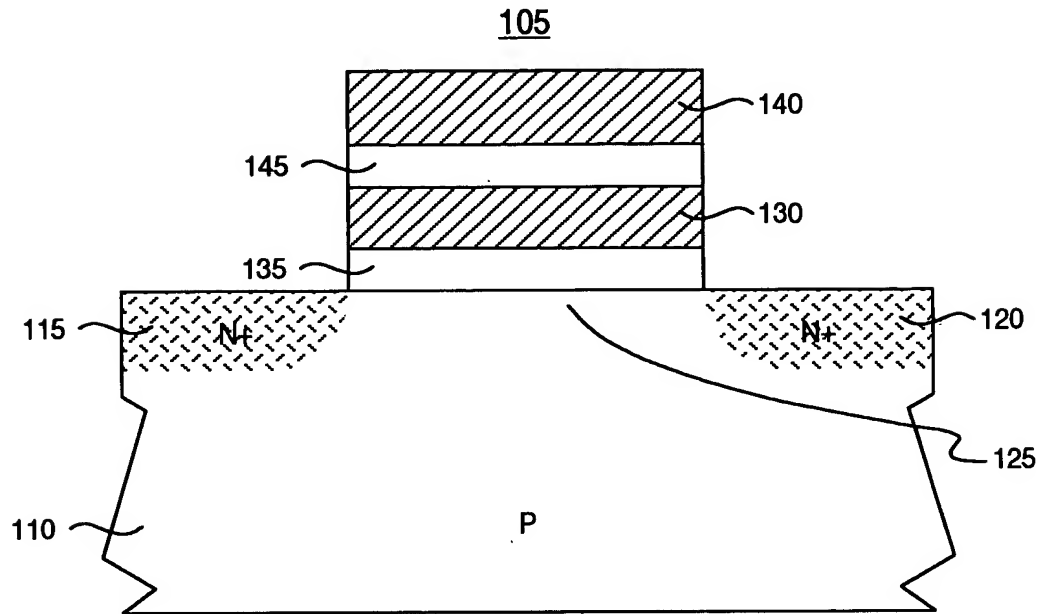


FIGURE 1A
(CONVENTIONAL ART)

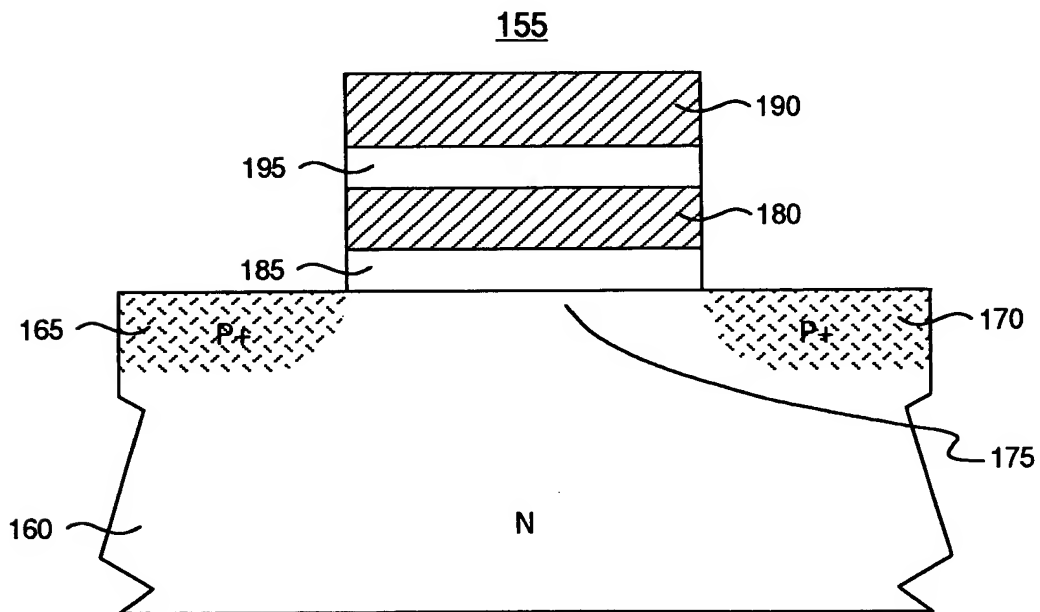
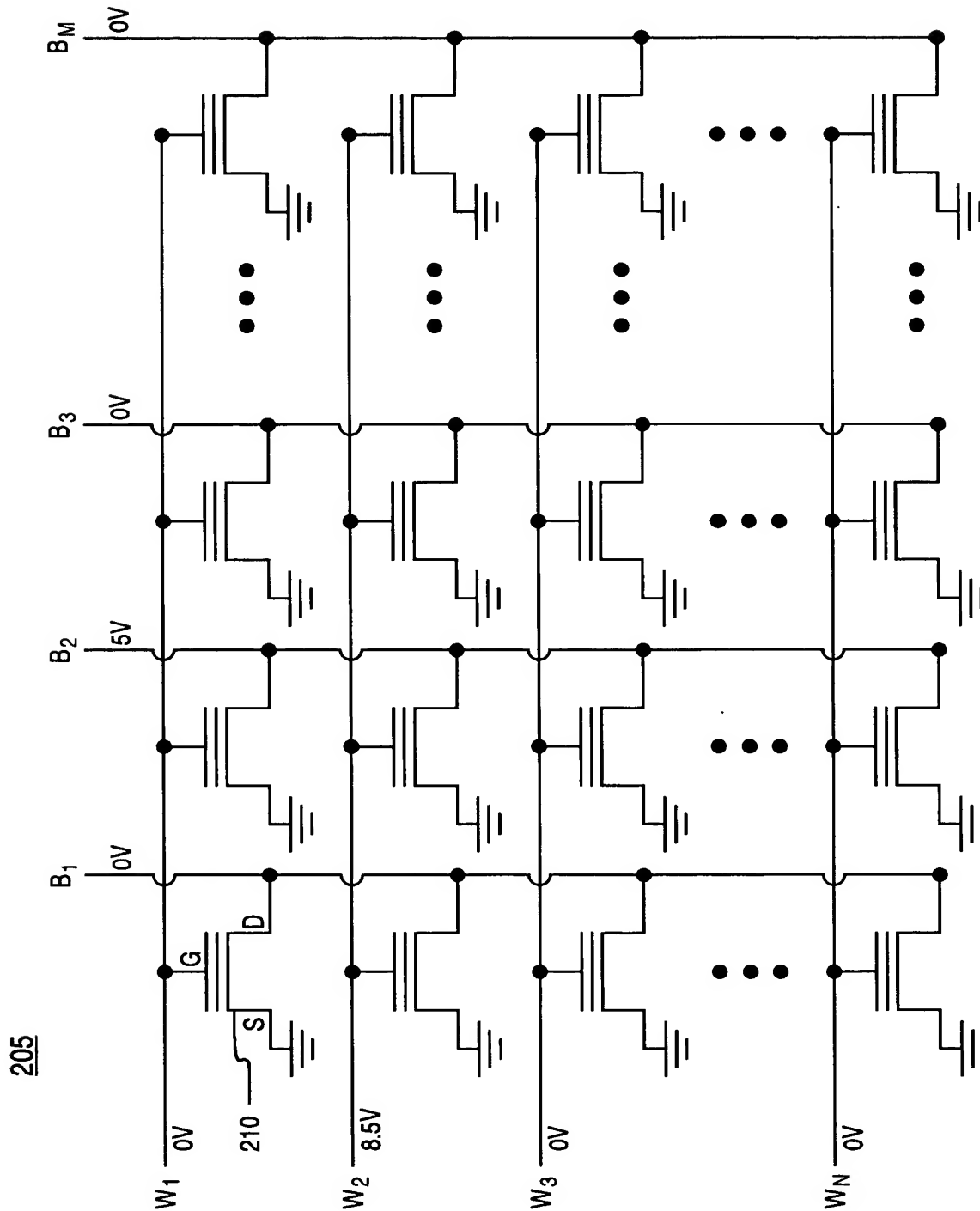


FIGURE 1B
(CONVENTIONAL ART)



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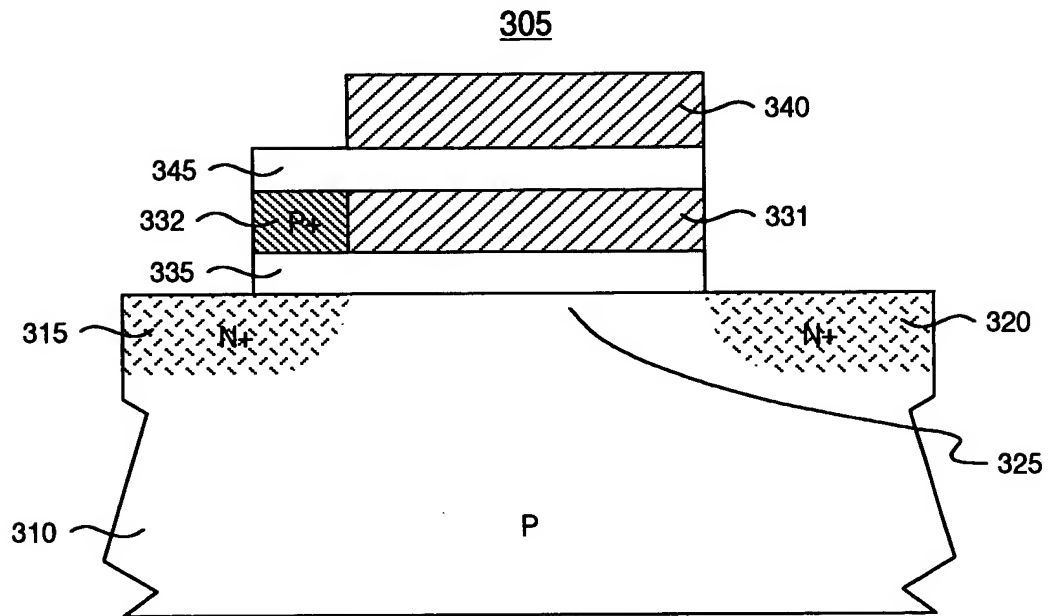


FIGURE 3

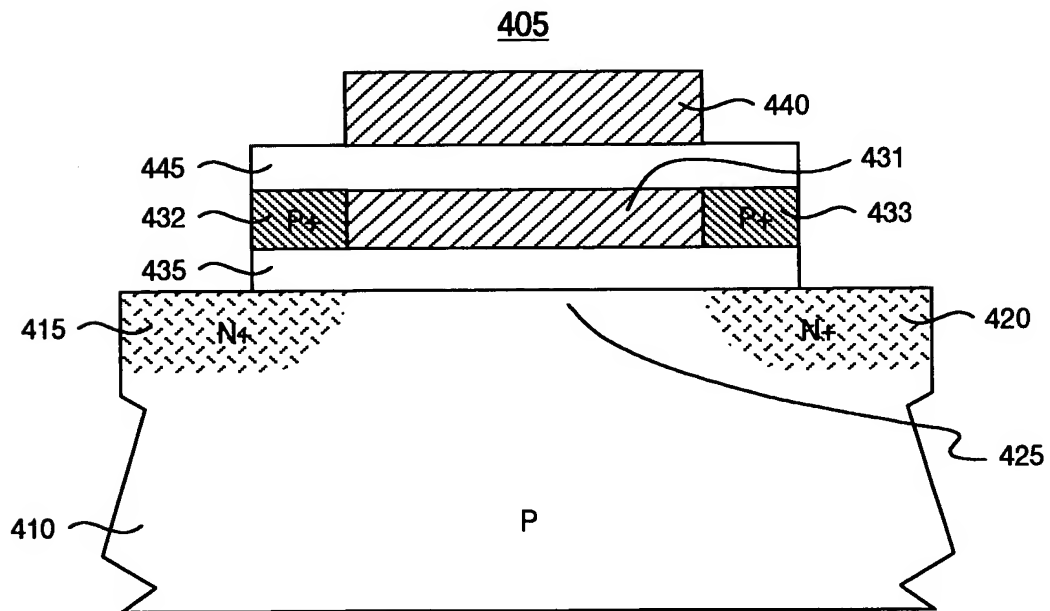


FIGURE 4

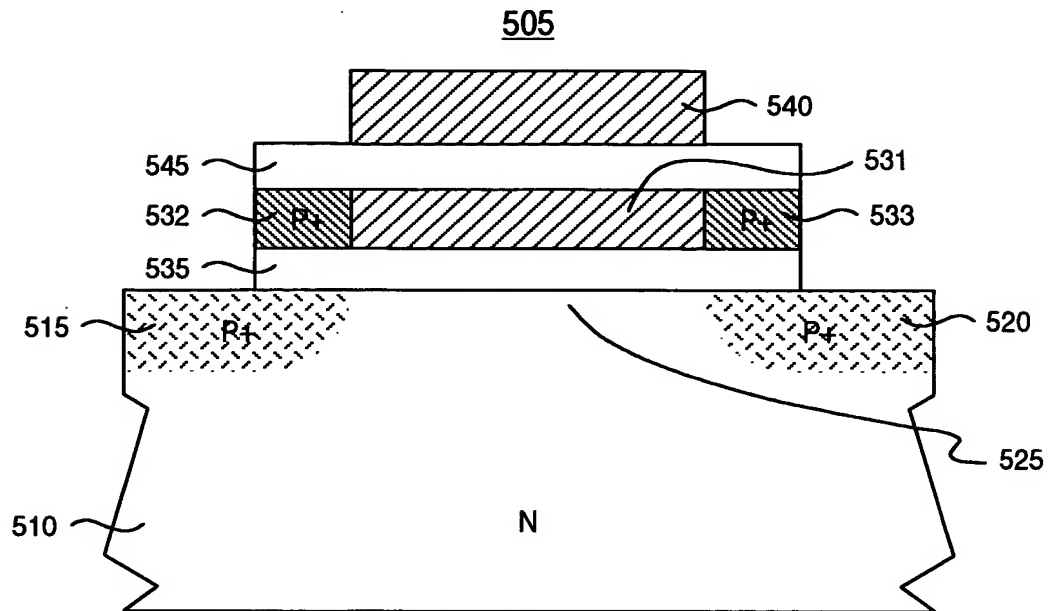


FIGURE 4

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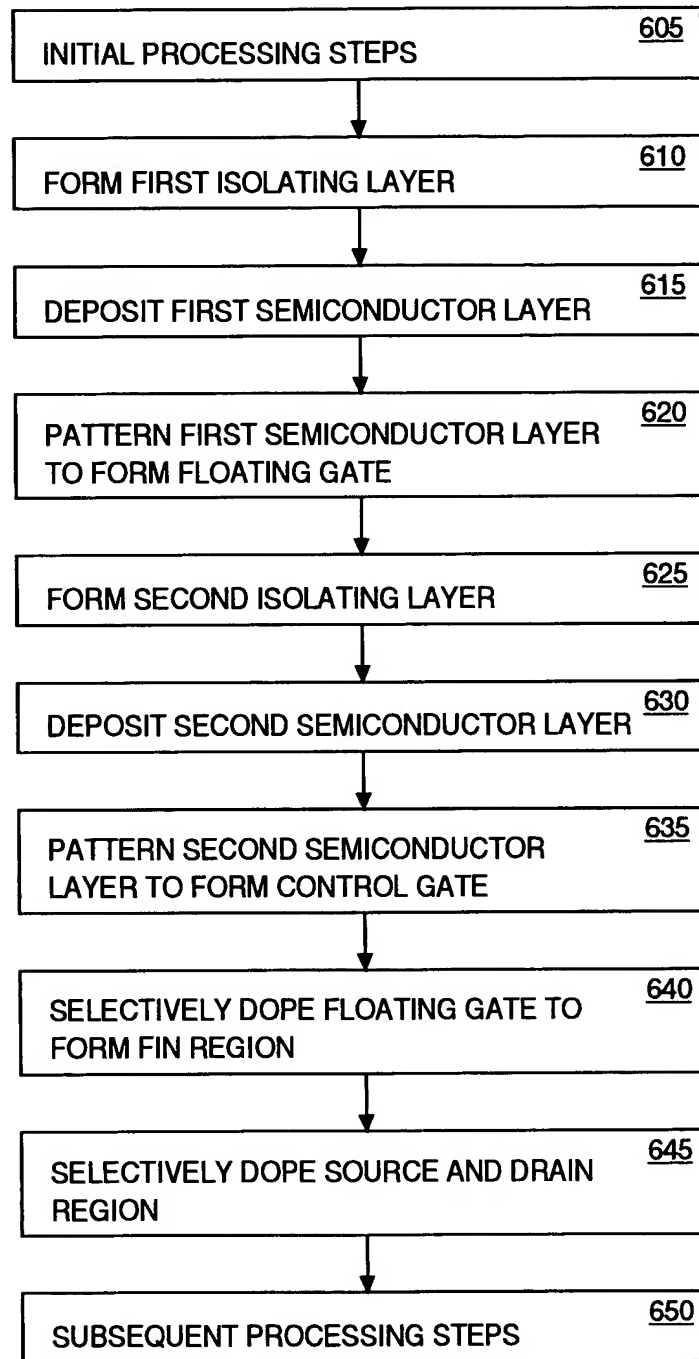


FIGURE 6